

## AMENDMENTS TO THE SPECIFICATION AND ABSTRACT

*In the specification, on page 9, lines 25-36 to page 10, lines 1-36 and page 11, line 1, please amend the paragraph as follows:*

### NUMERICAL REFERENCES

- ~~1, 14, 26, 30, 39~~ substrate
- ~~2, 102, 302, 401~~ first dielectric layer
- ~~3, 103, 303~~ first interface layer
- ~~4, 104~~ recording layer
- ~~5, 105, 305~~ second interface layer
- ~~6, 106, 306, 402~~ second dielectric layer
- ~~7~~ light absorption correction layer
- ~~8, 108~~ reflective layer
- ~~9, 27~~ adhesive layer
- ~~10, 28~~ dummy substrate
- ~~11~~ laser beam
- ~~12, 15, 22, 24, 29, 31, 32, 37~~ information recording medium
- ~~13~~ transparent layer
- ~~16, 18, 21~~ information layer
- ~~17, 19, 20~~ optical separation layer
- ~~23~~ first information layer
- ~~25~~ second information layer
- ~~33~~ spindle motor
- ~~34~~ objective lens
- ~~35~~ semiconductor laser
- ~~36~~ optical head
- ~~38~~ record/reproduce device
- ~~40~~ lower electrode
- ~~41, 204~~ first recording layer
- ~~42, 304~~ second recording layer
- ~~43~~ upper electrode

~~44, 51 electrical information recording medium~~  
~~45 application unit~~  
~~46, 59 resistance meter~~  
~~47, 49 switch~~  
~~48, 58 pulse power source~~  
~~50 electrical information record/reproduce device~~  
~~52 word line~~  
~~53 pit line~~  
~~54 memory cells~~  
~~55 address indicator circuit~~  
~~56 storage device~~  
~~57 external circuit~~  
~~107, 307 interface layer~~  
~~202 third dielectric layer~~  
~~203 third interface layer~~  
~~205 fourth interface layer~~  
~~206 fourth dielectric layer~~  
~~208 first reflective layer~~  
~~209 adjustable transmittance layer~~  
~~308 second reflective layer~~  
~~501, 502, 503, 504, 505, 508, 509 recording waveform~~  
~~506, 507 erasing waveform~~

*In the specification, page 17, lines 4-21, please amend the paragraph as follows:*

Interface layer 107 (not shown) can be placed between reflecting layer 108 and second dielectric layer 106. In this case, materials that can be used for interface layer 107 are those that have a lower thermal conductivity than the materials described for reflecting layer 108. When an Ag alloy is used for reflecting layer 108, for example Al or an Al alloy can be used for interface layer 107. Moreover, elements such as Cr, Ni, Si and C and the like, and oxides such as TiO<sub>2</sub>, ZrO<sub>2</sub>, HfO<sub>2</sub>, ZnO, Nb<sub>2</sub>O<sub>5</sub>, Ta<sub>2</sub>O<sub>5</sub>, SiO<sub>2</sub>, SnO<sub>2</sub>, Al<sub>2</sub>O<sub>3</sub>, Bi<sub>2</sub>O<sub>3</sub>, Cr<sub>2</sub>O<sub>3</sub>, Ga<sub>2</sub>O<sub>3</sub> and In<sub>2</sub>O<sub>3</sub> and the like

can be used in interface layer 107. Additionally, nitrides such as C-N, Ti-N, Zr-N, Nb-N, Ta-N, Si-N, Ge-N, Cr-N, Al-N, Ge-Si-N, Ge-Cr-N and the like can be used. In addition, sulfides such as ZnS and the like, carbides such as SiC and the like, fluorides such as LaF<sub>3</sub> and the like and carbon can also be used. Moreover, mixtures of the above materials can also be used. Additionally, a film thickness within the range 3 nm to 100 nm is preferred, with 10 nm to 50 nm being more preferred.

***In the specification, page 27, lines 4-7, please amend the paragraph as follows:***

It is satisfactory to position interface layer 307 (not shown) between second reflective layer 308 and second dielectric layer 306. Substantially the same materials as described for interface layer 107 in Embodiment 1 can be used in interface layer 307. Moreover, the function and form of the interface layer will also be substantially the same as for interface layer 107 of Embodiment 1.

***In the specification, page 29, lines 26-33, please amend the paragraph as follows:***

First, information layer 16 is formed over substrate 26 (of thickness 0.6 mm, for example). At this time, if a guide groove for the purpose of guiding laser beam 11 is to be formed in substrate 26, information layer 16 is formed on the side where the guide groove is formed. Specifically, substrate 26 is positioned within a coating device, and first dielectric layer 102, first interface layer 103, recording layer 104, second interface layer 105, second dielectric layer 106 and reflective layer 108 are laminated on sequentially. Furthermore, depending on the requirements, a film of interface layer 107 (not shown) is formed between second dielectric layer 106 and reflective layer 108. The methods for forming the films of the various layers are substantially the same as in Embodiment 1.

***In the specification, page 32, lines 15-23, please amend the paragraph as follows:***

Additionally, second information layer 25 is formed over substrate 30 (of thickness 0.6 mm, for example). At this time, if a guide groove for the purpose of guiding laser beam 11 is to be formed, second reflective layer 25 is formed on the side where the guide groove is formed. Specifically, substrate 30 is positioned within a coating device, and second reflective layer 308,

second dielectric layer 306, second interface layer 305, second recording layer 304, first interface layer 303 and first dielectric layer 302 are laminated on sequentially. Moreover, depending on the requirements, a film of interface layer 307 (not shown) can be formed between second reflective layer 308 and second dielectric layer 306. The methods for forming the films of the various layers are substantially the same as in Embodiment 3.

*In the specification, page 55, at the top of the page, the paragraph in Japanese language preceding the title "Claims," please amend as follows:*

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請求項及び明細書において、M3として列挙されている元素中にCrが重複しておりました。今回の英文原稿はPCT出願の翻訳文ですので、日本語原文に従ってそのまま訳しておりますが、万一、他の元素を意図しておられた場合には当方にお知らせ下さい。

*In the Abstract, please amend the paragraph as follows:*

An information recording medium with high recording sensitivity and superior repeat overwriting capability ~~is offered. For this purpose, in a~~ The information recording medium (15) comprising at least recording layer (104) ~~that records-recording and/or reproduces-reproducing~~ information through irradiation with a laser beam or ~~applyiation-application~~ of an electric current, and second dielectric layer (106) on substrate (14), wherein the second dielectric layer (106) comprises M1 (provided that M1 is at least one element selected from Sc, Y, La, Gd, Dy and Yb) and O.